

WHAT IS CLAIMED IS:

1. A capacitive-type semiconductor sensor comprising:

a single semiconductor substrate;

a plurality of sensor chips formed on the single substrate

5 and operable in respective single axes, each of the sensor chips having fixed electrodes and movable electrodes for producing a detection signal corresponding to capacitances between the fixed electrodes and the movable electrodes;

10 shared pads connected to the fixed electrodes of the plurality of the sensor chips and shared thereby; and

wirings connecting the fixed electrodes and the shared pads of the plurality of sensor chips are symmetrically formed.

2. The capacitive-type semiconductor sensor according to  
15 Claim 1, wherein two of the sensor chips are formed on the single substrate at an angle of 90 degrees to be operable in perpendicularly crossing directions.

3. The capacitive-type semiconductor sensor according to  
20 Claim 1, wherein two of the sensor chips are formed on the single substrate in parallel with each other to be operable in reverse directions.